Designer's™ Data Sheet

SWITCHMODE™ NPN Bipolar Power Transistor for Electronic Light Ballast and Switching Power Supply Applications

The MJE/MJF18204 have an application specific state—of—the—art die dedicated to the electronic ballast ("light ballast") and power supply applications.

- Improved Global Efficiency Due to Low Base Drive Requirements:
 - High and Flat DC Current Gain hFE
 - Fast Switching
 - No Coil Required in Base Circuit for Fast Turn-Off (No Current Tail)
- Full Characterization at 125°C
- Motorola "6 SIGMA" Philosophy Provides Tight and Reproducible Parametric Distributions
- Two Package Choices: Standard TO-220 or Isolated TO-220

MAXIMUM RATINGS

Rating	Symbol	MJE18204	MJF18204	Unit	
Collector–Emitter Voltage		VCEO	600		Vdc
Collector–Base Voltage		VCBO	12	00	Vdc
Collector–Emitter Voltage		VCES	12	00	Vdc
Emitter–Base Voltage		V _{EBO}	10		Vdc
Collector Current — Continuous — Peak (1)	S	I _{CM}	5 1		Adc
Base Current — Continuous — Peak (1)		I _B	2	=	Adc
$ \begin{array}{lll} \text{RMS Isolation Voltage (2)} & \text{Per Figure 22} \\ \text{(for 1 sec, R.H.} \leq 30\%) & \text{Per Figure 23} \\ \text{T}_{\text{C}} = 25^{\circ}\text{C} & \text{Per Figure 24} \\ \end{array} $		VISOL1 VISOL2 VISOL3		4500 3500 1500	Volts
*Total Device Dissipation @ T _C = 25°C *Derate above 25°C		PD	75 0.6	35 0.28	Watt W/°C
Operating and Storage Temperature		Т _J , Т _{stg}	-65 to 150		°C

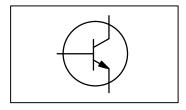
THERMAL CHARACTERISTICS

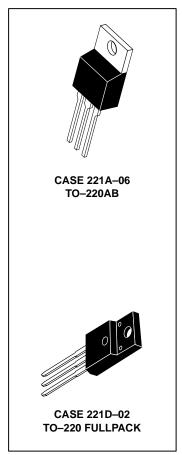
Rating	Symbol	MJE18204	MJF18204	Unit
Thermal Resistance — Junction to Case — Junction to Ambient	$R_{ heta JA}$	1.65 62.5	3.55 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	TL	26	60	°C

- (1) Pulse Test: Pulse Width = 5 ms, Duty Cycle ≤ 10%.
- (2) Proper strike and creepage distance must be provided.

MJE18204 MJF18204

POWER TRANSISTORS
5 AMPERES
1200 VOLTS
35 and 75 WATTS





Designer's Data for "Worst Case" Conditions — The Designer's Data Sheet permits the design of most circuits entirely from the information presented. SOA Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

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MJE18204 MJF18204

Characteristic			Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS							
Collector–Emitter Voltage (I _C = 1 mA, I _B = 0)			VCEO	600	660		Vdc
Collector–Emitter Sustaining Voltage (I _C = 100 mA, L = 25 mH) (I _C = 200 mA, L = 25 mH, R = 2 Ω)			VCEO(sus) VCER(sus)	550 600	630 700		Vdc
Collector–Base Breakdow (I _{CBO} = 1 mA, I _E = 0)	n Voltage		V _{СВО}	1200	1300		Vdc
Emitter–Base Breakdown (I _{EBO} = 1 mA, I _C = 0)	Voltage		V _{EBO}	10	12.9		Vdc
Collector Cutoff Current (\	V _{CE} = 600 V, I _B = 0) V _{CE} = 550 V, I _B = 0)	@ T _C = 25°C @ T _C = 125°C	ICEO			200 2000	μAdc
	V _{CE} = Rated V _{CES} , V _{BE} = 0) V _{CE} = 1000 V, V _{BE} = 0)	@ T _C = 25°C @ T _C = 125°C @ T _C = 125°C	ICES			100 500 100	μAdc
Collector Cutoff Current (V _{CB} = Rated V _{CB} , I _E =	= 0)		I _{CBO}			100	μAdc
Emitter–Cutoff Current (VEB = 10 Vdc, IC = 0)			IEBO			100	μAdc
ON CHARACTERISTICS							
Base–Emitter Saturation Voltage (I _C = 1 Adc, I _B = 0.1 Adc) (I _C = 2 Adc, I _B = 0.4 Adc)			V _{BE(sat)}		0.83 0.92	1.1 1.25	Vdc
Collector–Emitter Saturation (IC = 1 Adc, IB = 0.1 Add	@ T _C = 25°C @ T _C = 125°C	VCE(sat)		0.3 0.7	1 1.25	Vdc	
$(I_C = 2 \text{ Adc}, I_B = 0.4 \text{ Add})$	@ T _C = 25°C @ T _C = 125°C			0.3 0.8	0.6 1.25		
DC Current Gain (I _C = 0.5 Adc, V _{CE} = 3 \)	@ T _C = 25°C @ T _C = 125°C	hFE	18	23	35	_	
$(I_C = 1 \text{ Adc}, V_{CE} = 1 \text{ Vdc})$		@ T _C = 25°C @ T _C = 125°C		10 8	13	22	
(I _C = 2 Adc, V _{CE} = 1 Vd	@ T _C = 25°C @ T _C = 125°C		5 4	8 6		_	
(IC = 5 mAdc, VCE = 5 \	@ T _C = 25°C @ T _C = 125°C		10	25 33		_	
DYNAMIC CHARACTERIS	TICS						•
Current Gain Bandwidth (I _C = 0.5 Adc, V _{CE} = 10 Vdc, f = 1 MHz)			fT		13		MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1 MHz)			C _{ob}			200	pF
Input Capacitance (V _{EB} = 8 Vdc)			C _{ib}			2000	pF
DYNAMIC SATURATION VOLTAGE Dynamic Saturation IC = 2 Adc @ 3 μs		@ T _C = 25°C	Vo=(4- 1)		2.5	l	V
Dynamic Saturation Voltage: Determined 1 μs and 3 μs respectively after rising I _{B1} reaches	$I_{C} = 2 \text{ Adc}$ @ 3 µs $I_{B1} = 660 \text{ mAdc}$ $V_{CC} = 300 \text{ V}$	@ T _C = 25°C	VCE(dsat)		7.5		
	I _C = 2 Adc @ 3 μs I _{B1} = 0.4 Adc	@ T _C = 25°C			7]
90% of final I _{B1}	ACC = 300 A	@ T _C = 125°C			15		

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

	Symbol	Min	Тур	Max	Unit		
SWITCHING CHARAC	TERISTICS: Resistive Load (D.C.:	≤ 10%, Pulse Width	n = 20 μs)		•	•	
Turn-on Time	I _C = 2 Adc, I _{B1} = 0.4 Adc	@ T _C = 25°C	ton		105	175	ns
Turn-off Time	I _{B2} = 1 Adc V _{CC} = 300 Vdc	@ T _C = 25°C	^t off		1.75	2.5	μs
Turn-on Time	I _C = 2 Adc, I _{B1} = 0.4 Adc	@ T _C = 25°C	ton		95	200	ns
Turn-off Time	I _{B2} = 0.4 Adc V _{CC} = 300 Vdc	@ T _C = 25°C	^t off		3.5	4.5	μs
Turn-on Time	la 0.7 Ado la	@ T _C = 25°C	^t d		70	150	ns
	$I_C = 0.7 \text{ Adc}, I_{B1} = 50 \text{ mAdc}$ $I_{B2} = 0.4 \text{ Adc}$	@ 1C = 25 C	t _r		210	400	ns
Turn-off Time	V _{CC} = 125 Vdc PW = 70 μs	@ T _C = 25°C	t _S		0.9	1.2	μs
	1 νν = 70 μs		t _f		275	450	ns
WITCHING CHARAC	TERISTICS: Inductive Load (Vclan	np = 300 V, V _{CC} =	15 V, L = 200 μH	1)			
Fall Time		@ T _C = 25°C @ T _C = 125°C	t _f		110 95	175	ns
Storage Time	I _C = 1 Adc I _{B1} = 0.1 Adc I _{B2} = 0.5 Adc	@ T _C = 25°C @ T _C = 125°C	t _S		1.35 1.9	2	μs
Crossover Time		@ T _C = 25°C @ T _C = 125°C	t _C		150 115	250	ns
Fall Time		@ T _C = 25°C @ T _C = 125°C	t _f		120 180	200	ns
Storage Time	I _C = 2 Adc I _{B1} = 0.4 Adc I _{B2} = 1 Adc	@ T _C = 25°C @ T _C = 125°C	t _S		1.9 2.35	2.75	μs
Crossover Time		@ T _C = 25°C @ T _C = 125°C	t _C		190 180	300	ns
Fall Time	I _C = 2 Adc	@ T _C = 25°C	t _f		185	300	ns
Storage Time	I _{B1} = 0.4 Adc	@ T _C = 25°C	t _S		4	5	μs
Crossover Time	$I_{B2} = 0.4 \text{ Adc}$	@ T _C = 25°C	t _C		350	500	ns

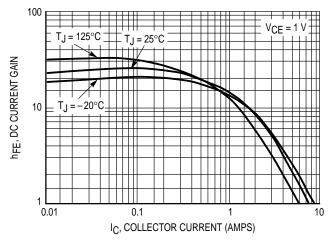


Figure 1. DC Current Gain @ 1 Volt

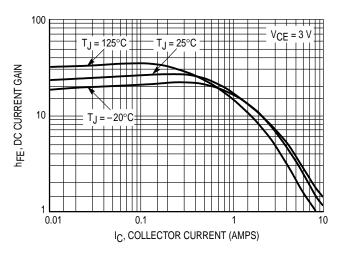


Figure 2. DC Current Gain @ 3 Volts

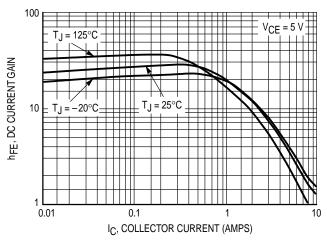


Figure 3. DC Current Gain @ 5 Volts

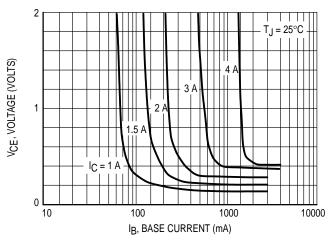


Figure 4. Collector Saturation Region

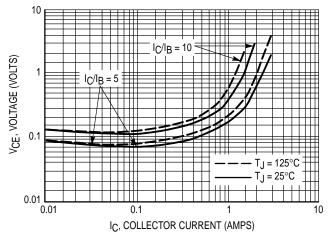


Figure 5. Collector-Emitter Saturation Voltage

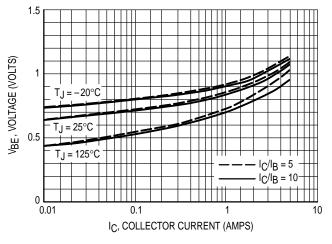


Figure 6. Base-Emitter Saturation Region

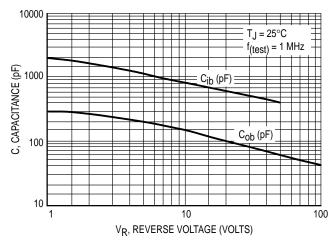


Figure 7. Capacitance

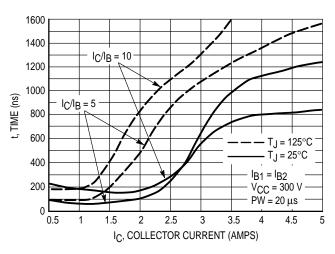


Figure 8. Resistive Switching, ton

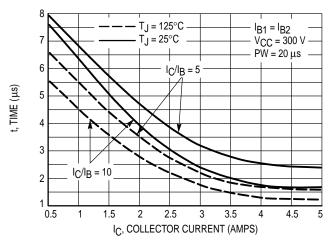


Figure 9. Resistive Switching, toff

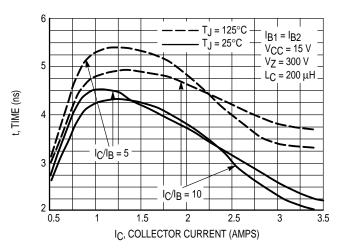


Figure 10. Inductive Storage Time, tsi

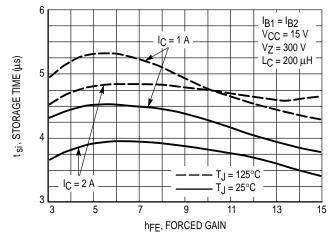


Figure 11. Inductive Storage Time, tSi (hFE)

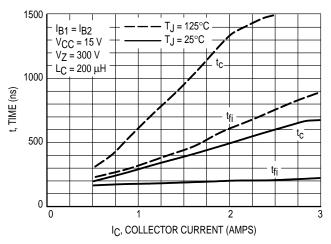


Figure 12. Inductive Switching, $t_C \& t_{fi} @ I_C/I_B = 5$

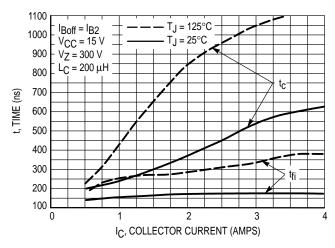


Figure 13. Inductive Switching, $t_C \& t_{fi} @ I_C/I_B = 10$

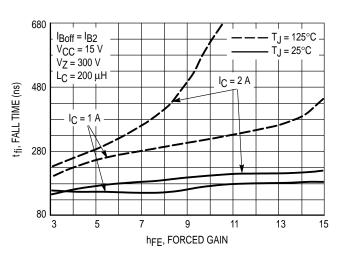


Figure 14. Inductive Fall Time

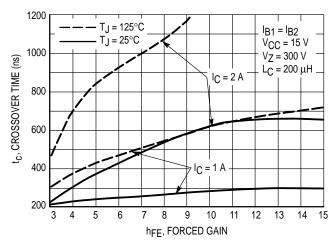


Figure 15. Inductive Crossover Time

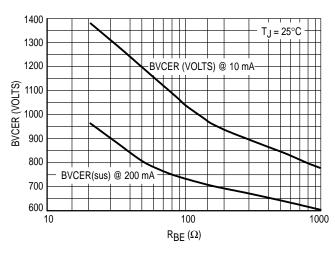


Figure 16. BVCER = f (RBE)

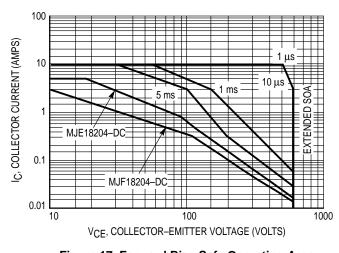


Figure 17. Forward Bias Safe Operating Area

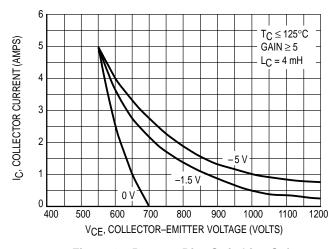


Figure 18. Reverse Bias Switching Safe Operating Area

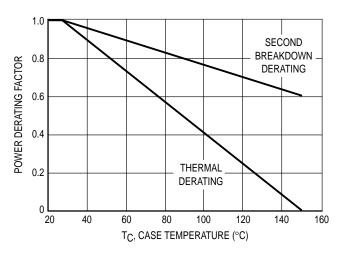


Figure 19. Forward Bias Power Derating

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_{C} – V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate. The data of Figure 19 is based on $T_{C} = 25^{\circ}C$; $T_{J}(pk)$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated when $T_{C} > 25^{\circ}C$. Second breakdown limitations do not derate the same as thermal limitations. Allowable current at the voltages shown on Figure 16 may be found at any case temperature by using the appropriate curve on Figure 18.

TJ(pk) may be calculated from the data in Figures 21 and 22. At any case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown. For inductive loads, high voltage and current must be sustained simultaneously during turn–off with the base–to–emitter junction reverse biased. The safe level is specified as a reverse–biased safe operating area (Figure 17). This rating is verified under clamped conditions so that the device is never subjected to an avalanche mode.

TYPICAL SWITCHING CHARACTERISTICS (IB1 = IB2 FOR ALL CURVES)

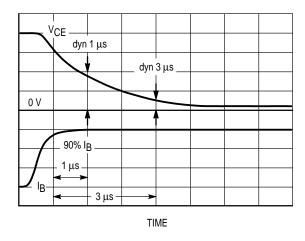


Figure 20. Dynamic Saturation Voltage Measurements

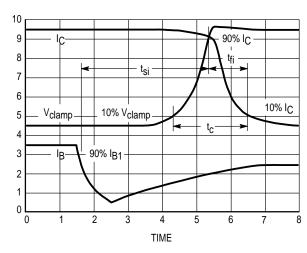
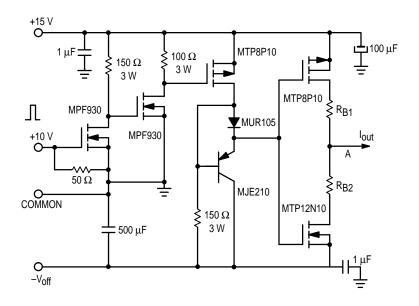
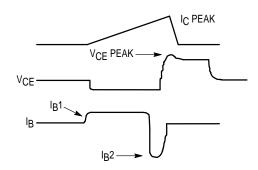


Figure 21. Inductive Switching Measurements

TYPICAL SWITCHING CHARACTERISTICS (IB1 = IB2 FOR ALL CURVES)

Table 1. Inductive Load Switching Drive Circuit





V(BR)CEO(sus) L = 10 mH
_

 $R_{B2} = \infty$ V_{CC}^{--} = 20 Volts $I_{C(pk)} = 100 \text{ mA}$

Inductive Switching

 $L = 200 \mu H$ $R_{B2} = 0$ $V_{CC} = 15 \text{ Volts}$ R_{B1} selected for desired I_{B1}

RBSOA

 $L = 500 \mu H$ $R_{B2} = 0$ $V_{CC} = 15 \text{ Volts}$

R_{B1} selected for desired I_{B1}

TYPICAL THERMAL RESPONSE (IB1 = IB2 FOR ALL CURVES)

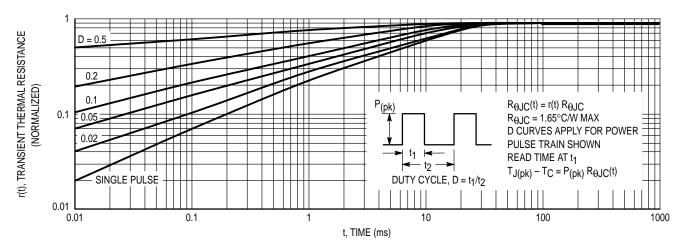


Figure 22. Typical Thermal Response ($Z_{\theta JC}(t)$) for MJE18204

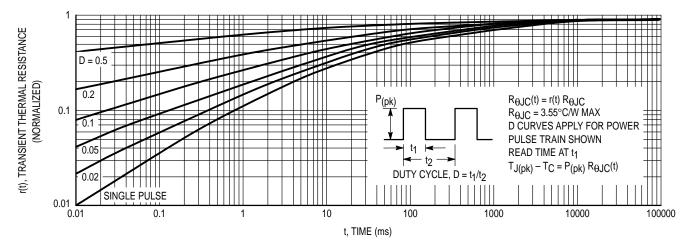
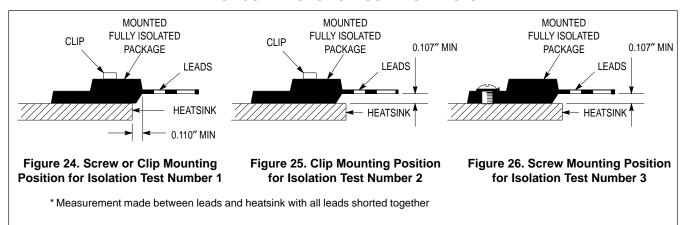


Figure 23. Typical Thermal Response (Z₀JC(t)) for MJF18204

TEST CONDITIONS FOR ISOLATION TESTS*



MOUNTING INFORMATION**

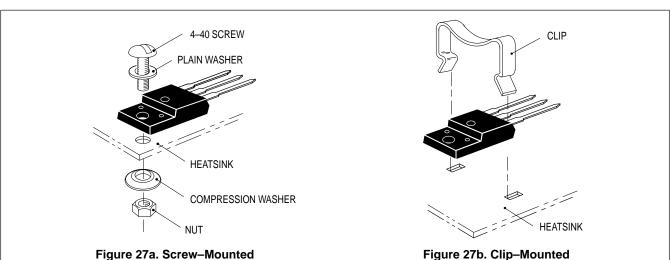


Figure 27. Typical Mounting Techniques for Isolated Package

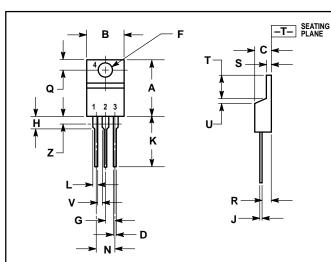
Laboratory tests on a limited number of samples indicate, when using the screw and compression washer mounting technique, a screw torque of 6 to 8 in · lbs is sufficient to provide maximum power dissipation capability. The compression washer helps to maintain a constant pressure on the package over time and during large temperature excursions.

Destructive laboratory tests show that using a hex head 4–40 screw, without washers, and applying a torque in excess of 20 in • lbs will cause the plastic to crack around the mounting hole, resulting in a loss of isolation capability.

Additional tests on slotted 4–40 screws indicate that the screw slot fails between 15 to 20 in · lbs without adversely affecting the package. However, in order to positively ensure the package integrity of the fully isolated device, Motorola does not recommend exceeding 10 in · lbs of mounting torque under any mounting conditions.

^{**} For more information about mounting power semiconductors see Application Note AN1040.

PACKAGE DIMENSIONS

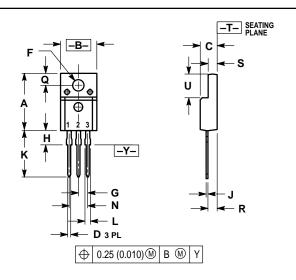


- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080	_	2.04

STYLE 1: PIN 1. BASE 2. COLLECTOR
3. EMITTER
4. COLLECTOR

CASE 221A-06 TO-220AB **ISSUE Y**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.621	0.629	15.78	15.97
В	0.394	0.402	10.01	10.21
С	0.181	0.189	4.60	4.80
D	0.026	0.034	0.67	0.86
F	0.121	0.129	3.08	3.27
G	0.100 BSC		2.54 BSC	
Н	0.123	0.129	3.13	3.27
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.14	1.52
N	0.200	BSC	5.08 BSC	
Q	0.126	0.134	3.21	3.40
R	0.107	0.111	2.72	2.81
S	0.096	0.104	2.44	2.64
U	0.259	0.267	6.58	6.78

STYLE 1:

PIN 1. GATE

2. DRAIN 3. SOURCE

CASE 221D-02 (ISOLATED TO-220 TYPE) **UL RECOGNIZED: FILE #E69369 ISSUE D**

MJE18204 MJF18204

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